

N-channel TrenchMOS standard level FET

23 November 2020

**Product data sheet** 

### 1. General description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS technology.

### 2. Features and benefits

· Low on-state resistance in a small surface mount package

### 3. Applications

• DC-to-DC primary side switching

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C < T <sub>j</sub> < 150 °C	-	-	100	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> = 25 °C	-30	-	30	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C	-	-	1.9	А
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	213	250	mΩ
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C	-	-	2	W

# nexperia

### 5. Pinning information

Table 2	2. Pinning info	rmation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D .
2	S	source		
3	D	drain		G mbb076 S

### 6. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV213SN		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PMV213SN	%2N

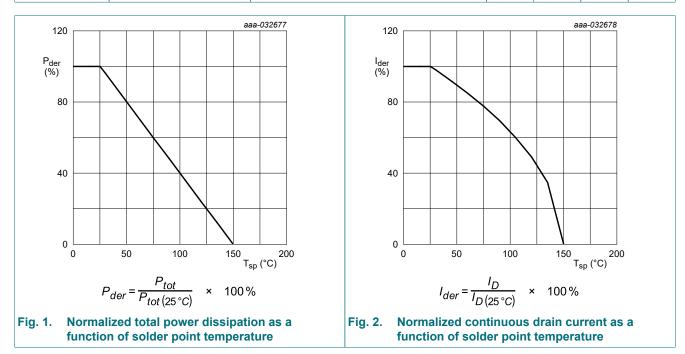
[1] % = placeholder for manufacturing site code

### 8. Limiting values

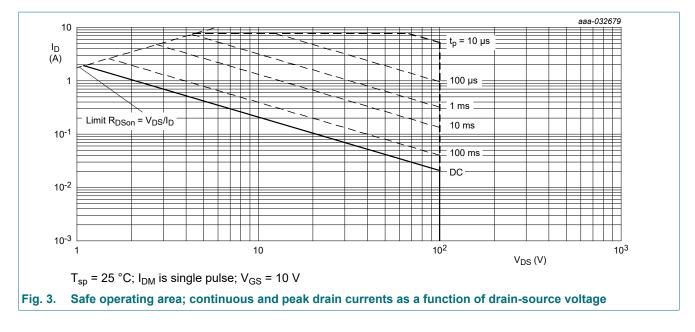
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C < T <sub>j</sub> < 150 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ; 25 °C < T <sub>j</sub> < 150 °C	-	100	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> = 25 °C	-30	30	V
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C	-	1.9	A
		V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 100 °C	-	1.2	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$	-	7.6	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C	-	2	W
Tj	junction temperature		-55	150	°C
T <sub>stg</sub>	storage temperature		-55	150	°C
Source-drain	n diode		I		
Is	source current	T <sub>sp</sub> = 25 °C	-	1.7	А
I <sub>SM</sub>	peak source current	single pulse; t <sub>p</sub> ≤ 10 µs; T <sub>sp</sub> = 25 °C	-	6.9	Α



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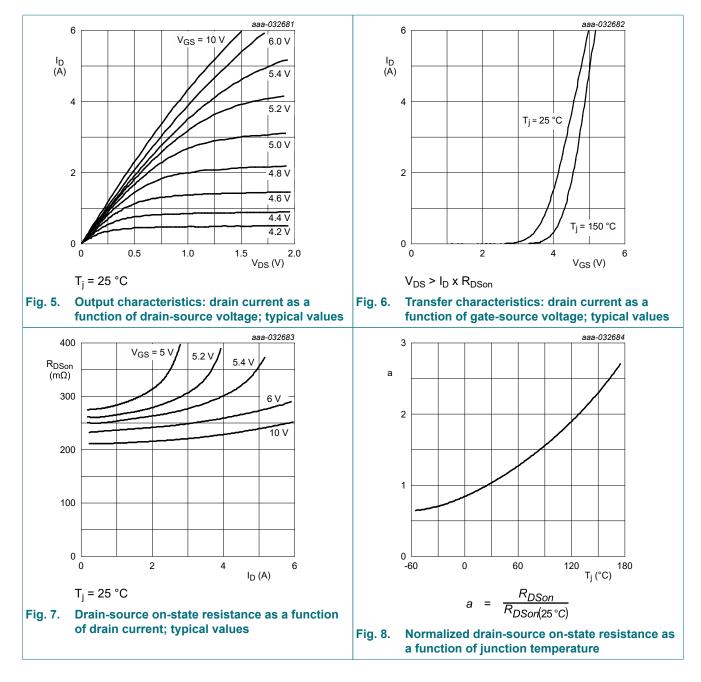


### 9. Thermal characteristics

Symbol	Parameter	Conditions		Γ	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-		-	60	K/W
10 <sup>2</sup>						a	aa-032680	
Z <sub>th(i-sp)</sub>								
Z <sub>th(j-sp)</sub> (K/W) duty	cycle = 0.5							
10 0.20								
-0.10								
0.02								
sing	le pulse							
1	10-3	10-2	10 <sup>-1</sup>		1	t <sub>p</sub> (s)	10	

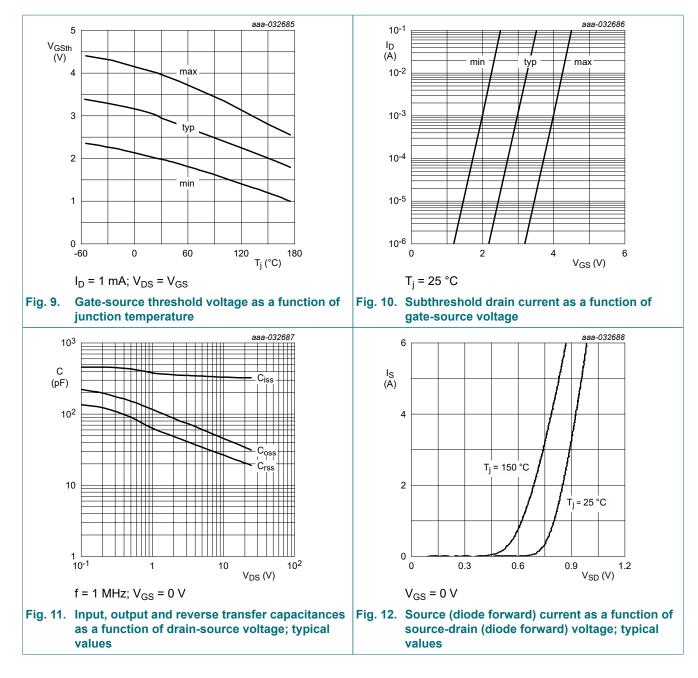
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	100	-	-	V
breakdown voltage	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	90	-	-	V
V <sub>GSth</sub> gate-source thre voltage	gate-source threshold	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	2	3	4	V
	voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C	1.2	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-10	-100	μA
R <sub>DSon</sub> drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 0.5 A; T <sub>j</sub> = 25 °C	-	213	250	mΩ	
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 0.5 A; T <sub>j</sub> = 150 °C	-	490	575	mΩ
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 80 V; I <sub>D</sub> = 1.2 A; V <sub>GS</sub> = 10 V;	-	7	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.4	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge		-	2.5	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	330	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	36	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	22	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 33 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	5.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	9.5	-	ns
t <sub>f</sub>	fall time	1	-	3	-	ns
Source-drai	in diode	· · ·	1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1.5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.83	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 1.2 A; dI <sub>S</sub> /dt = -100 A/μs;	-	36	-	ns
Q <sub>r</sub>	recovered charge	V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	23	-	nC

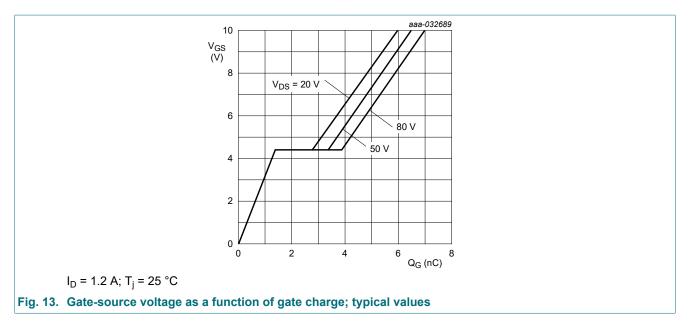


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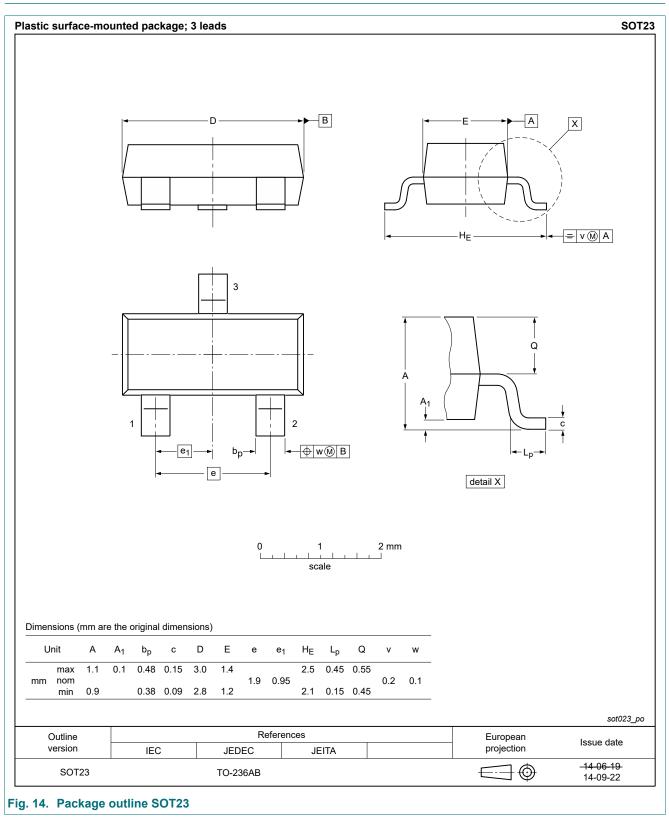
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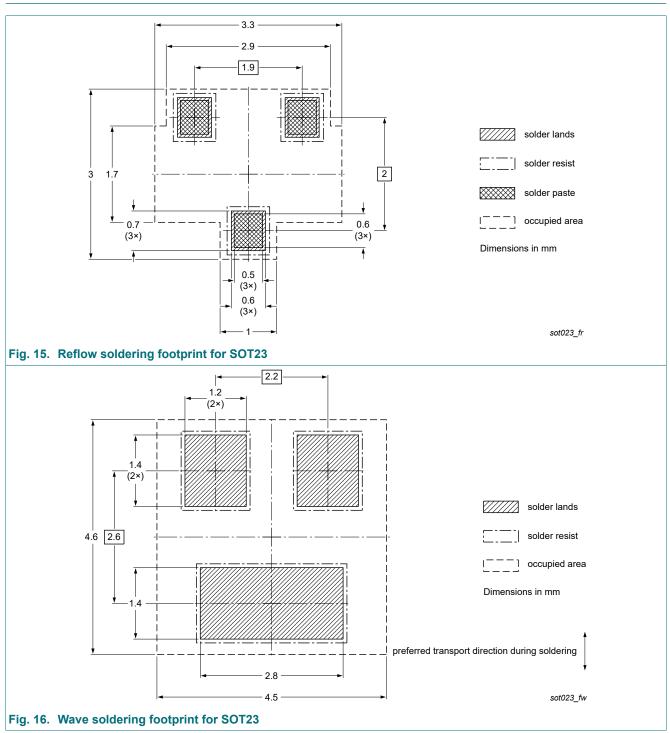
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### 11. Package outline



### 12. Soldering



### **13. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMV213SN v.3	20201123	Product data sheet	-	PMV213SN v.2		
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
PMV213SN v.2	20030219	Product data sheet	-	PMV213SN v.1		
PMV213SN v.1	20030115	Product data sheet	-	-		

### 14. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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### Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Characteristics	6
11. Package outline	10
12. Soldering	
13. Revision history	
14. Legal information	

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